MSKSEMI















ESD

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Broduct data sheet



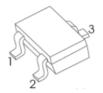
SS8050W













\$\$8050W TRANSISTOR (NPN)

FEATURES

Complimentary to SS8550W

MARKING: Y1

1. BASE 2. EMITTER

3. COLLECTOR

SOT-323

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current	1.5	Α
Pc	Collector Power Dissipation	250	mW
R _{OJA}	Thermal Resistance From Junction To Ambient	500	°C/W
T_J, T_stg	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V_{EB} = 5V, I_{C} =0			0.1	μA
DC ourrent gain	h _{FE(1)}	V _{CE} =1V, I _C = 100mA	120		400	
DC current gain	h _{FE(2)}	V _{CE} =1V, I _C = 800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B = 80mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =800mA, I _B = 80mA			1.2	V
Transition frequency	f⊤	V _{CE} =10V, I _C = 50mA, f=30MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0,f=1MHz			15	pF

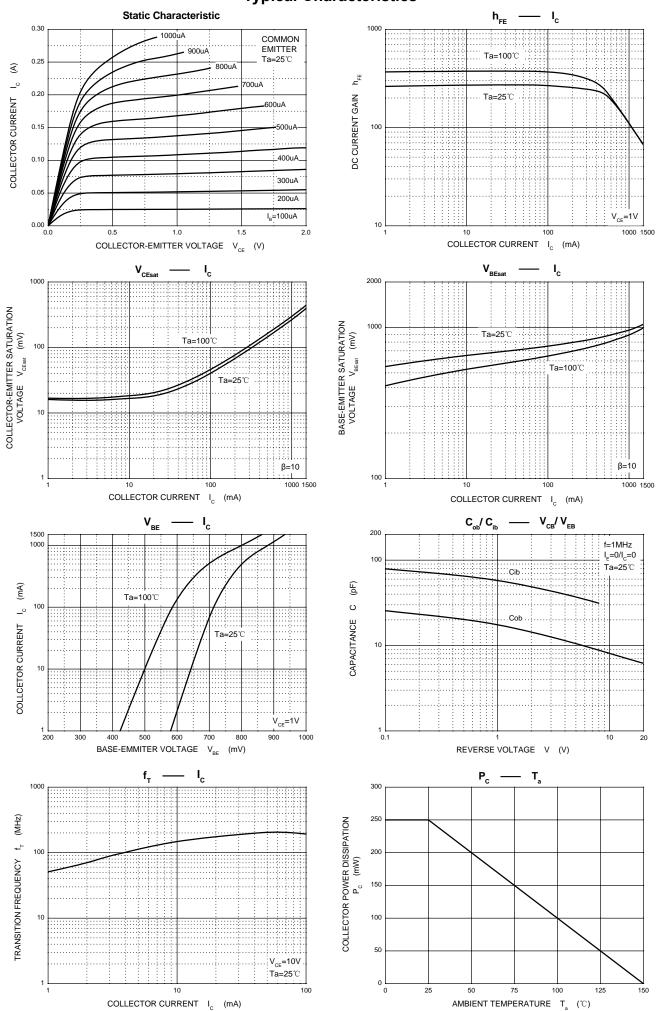
CLASSIFICATION OF hfe(1)

Rank	L	Н	J
Range	120-200	200-350	300-400

Semiconductor

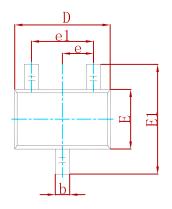


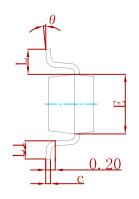
Typical Characteristics

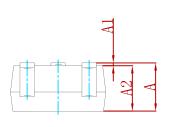




PACKAGE MECHANICAL DATA

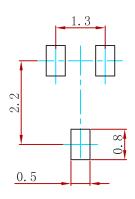






Compleal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.65	0 TYP	0.026	3 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SS8050W	SOT-323	3000



Semiconductor

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